R. Jacob Baker, Ph.D., P.E. Samsung Electronics vs. Promos Technologies 1 UNITED STATES PATENT AND TRADEMARK OFFICE 2 BEFORE THE PATENT TRIAL AND APPEAL BOARD 3 4 5 6 SAMSUNG ELECTRONICS, CO.,)) LTD., 7) Petitioner,) 8) Case No. IPR2019-00780 vs.) 9) Patent 6,163,492 PROMOS TECHNOLOGIES, INC.,) 10) Patent Owner.) 11 12 13 14 DEPOSITION OF R. JACOB BAKER, Ph.D., P.E. 15 Taken at the Office of: 16 17 Regus - Howard Hughes Parkway 18 3960 Howard Hughes Parkway, Suite 500 19 Las Vegas, Nevada 89169 20 21 Friday, October 25, 2019 22 8:54 a.m. 23 Reported By: 24 Gale Salerno, RMR, CCR No. 542 25 Job No. 10061825

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1		PREVIOUS	LY MARKED	EXHIBITS	IDENTIFIED	
2			(NOT A	TTACHED)		
3	Baker				Iden	ntified
4	Exhibit	1001 '	492 Patent			5
5	Exhibit	1006 M	cAdams U.S	. Patent	4,621,346	27
6	Exhibit	1007 U	da, United	States I	Patent	38
7	Exhibit	5,519,658	22			
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R. Jacob Baker, Ph.D., P.E. Samsung Electronics vs. Promos Technologies 1 DEPOSITION OF R. JACOB BAKER, Ph.D., P.E. October 25, 2019 2 3 4 5 EXAMINATION 6 BY MR. JONES: 7 Q. Good morning. 8 Α. Good morning. 9 We've been through the same circus many Ο. times, but again, it's Kevin Jones for ProMOS today. 10 11 Can you state your name for the record. 12 Russel, with one L, Jacob Baker. Α. 13 And is it your understanding that you are Q. 14 here today to testify about declarations that you submitted related to the, I'll call it '492 patent, 15 which is 6,163,492? 16 17 Α. Yes. 18 And you submitted three declarations ο. 19 related to the '492 patent, correct? 20 Α. Yes. 21 And I'll just review a few of the basic 0. 22 ground rules just basically to get them on the record, although I know that you're well familiar 23 with them. 24 25 The general format is that I would like to

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1	get answers to the questions I ask. And if you can
2	wait for me to complete my question before answering,
3	the record will be more clear. Okay?
4	A. Yes.
5	Q. And if you need a break at any time, just
6	say so. I'll generally take breaks every 60 or 90
7	minutes.
8	A. Okay.
9	Q. Is there any reason that you can't give
10	complete and accurate testimony today?
11	A. No.
12	Q. I see you have some papers in front of you.
13	Can you tell me what they are?
14	A. These are clean copies of my declarations
15	for these three IPRs.
16	Q. Do you mind if I take a ten-second look?
17	A. Nope.
18	Q. There you go.
19	A. Thank you.
20	Q. So I would like to start by handing you the
21	'492 patent, which is Exhibit 1001.
22	(Exhibit 1001 was identified.)
23	MR. ANDERSON: Do you have an extra one?
24	I'll take it.
25	MR. JONES: I have two copies of each.

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1		MR. ANDERSON: Are you sure?
2		MR. JONES: I have mine. I brought it for
3	you guys.	
4		MR. ANDERSON: Thank you.
5		MR. JONES: I'm not going to carry it home.
6	BY MR. JO	NES:
7	Q.	Dr. Baker, are you familiar with the '492
8	patent?	
9	Α.	Yes.
10	Q.	And I would like to start by talking about
11	Figure 1.	
12	Α.	Okay.
13	Q.	And just generally ask and this may
14	relate to	columns 1 and 2 as well, but I want to
15	generally	ask what the problem that the '492
16	described	was with the circuit of Figure 1 labeled
17	prior art	?
18	Α.	It's not clearly described in the patent,
19	but I thin	nk that having read the patent, that they're
20	trying to	solve the problem of the out voltage
21	remaining	high after the fuse F-1 in Figure 1 has
22	been blown	ı.
23	Q.	And is that a problem that exists before
24	the circu:	it is being read or used?
25		MR. ANDERSON: Objection. Form.

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1	THE WITNESS: I don't know how to answer
2	that. The problem is if OUT remains high after the
3	fuse is blown, there's no difference between the fuse
4	being blown and the fuse not being blown.
5	BY MR. JONES:
6	Q. Okay. What would be the reason or reasons
7	that OUT may go high if the fuse was blown?
8	A. So one reason is discussed in Column 1 of
9	the '492, roughly lines 43, that OUT may become
10	unstable due to capacitive coupling during
11	operations.
12	Q. Does the '492 state any other reasons that
13	the voltage on OUT may go high when the fuse was
14	blown?
15	A. I don't recall there being a specific
16	detailed discussion of why the voltage may remain
17	high when the fuse is blown in the patent. But if
18	you point me to it, I'll take a look.
19	Q. Okay. You did mention the concept of
20	capacitive coupling in Column 1, lines 43 and 44.
21	What does that mean in this context?
22	A. If we look at Figure 1, and the fuse is
23	programmed or blown, that as Vdd goes from say zero
24	to 5 volts, there may be a capacitance from Vdd to
25	the OUT node. And so by raising Vdd from zero to 5,

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1	it could capacitively or couple to OUT, raising OUT
2	with Vdd.
3	Q. Other than from Vdd, is there capacitive
4	coupling from other sources that could affect voltage
5	at OUT?
6	A. I don't think so, but if you give me a
7	specific example, I'll think about it.
8	Q. For example, OUT connects to something down
9	the stream to the left of the circuit, correct?
10	A. Presumably, yes.
11	Q. And are there is there capacitive
12	coupling from whatever OUT connects to that will
13	affect the voltage on OUT?
14	A. That isn't related to Vdd changing?
15	Q. Yes, that is not related to Vdd changing.
16	A. I don't think so.
17	Q. Is there capacitive coupling from ground to
18	OUT that may affect the voltage on OUT?
19	A. There may be capacitive coupling from
20	ground to OUT, but it wouldn't have any influence
21	because ground doesn't vary.
22	Q. Does Vdd vary?
23	MR. ANDERSON: Objection. Form.
24	THE WITNESS: Vdd should remain constant.
25	But if there are circuits which all of a sudden pull

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1	a lot of current, there could be some minor variation
2	in Vdd that's due to the large current that flows
3	from the circuits pulling current from Vdd.
4	But in general, the answer is no, Vdd
5	doesn't vary unless you're powering up the circuit
6	and turning it on.
7	BY MR. JONES:
8	Q. Okay. Now, I would like to look at
9	Figure 2A, and also with reference to the
10	specification, I'm sure, and ask you how Figure 2A is
11	an improvement in solving that problem that we talked
12	about in Figure 1?
13	A. I don't know if I would agree that Figure
14	2A is an improvement over Figure 1.
15	For example, the diode has more
16	capacitance, and so with the power supply voltage
17	VINT internal changing or going from zero to Vdd,
18	there would actually be more capacitive coupling to
19	OUT with the diode there.
20	So I don't know if I would agree that this
21	is necessarily an improvement over Figure 1.
22	Q. What does the specification say the purpose
23	of the diode 234 is?
24	A. So in Column 3, roughly lines starting at
25	33 roughly, the diode is connected to the terminal

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1	OUT and to the internal power supply VINT terminal
2	212. So that when power is off, the diode will limit
3	OUT to one threshold roughly .6, .7. It will limit
4	OUT to .6, .7 of the internal power supply.
5	In this example where they're saying the
6	internal power supply is grounded, it would limit OUT
7	to the threshold above ground.
8	Q. And is that voltage limit which you said is
9	about .6 or .7 volts in this embodiment enough to
10	turn on transistor 230 in Figure 2A?
11	A. So we've kind of changed the subject. So
12	we've limited OUT to .6, .7, and now you're saying
13	the internal power supply is powered up, and you're
14	asking if with internal power supply powered up, if
15	.6, .7 volts is enough to turn transistor 230 on in
16	Figure 2A?
17	Q. Not exactly. So let me kind of strike the
18	last little discussion and start over.
19	A. Okay.
20	Q. Regardless of whether VINT is powered up or
21	not, I just want to know in this embodiment if the
22	value of OUT is .6 or .7 volts, will that turn on
23	transistor 230?
24	MR. ANDERSON: Objection. Form.
25	THE WITNESS: If I understand your question

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1	correctly, the answer is no. It's too low of a
2	voltage.
3	BY MR. JONES:
4	Q. Just to make sure I understand your answer,
5	would your answer be different if I restricted it to
6	VINT to being powered up?
7	A. I think the answer would be the same, but
8	230 wouldn't turn on if the output is a low voltage
9	like .6 volts.
10	Q. And in Column 3, you pointed me to a
11	discussion sort of in the middle of the column about
12	the diode. And for example, the paragraph at 333 to
13	49, is this paragraph saying that the diode will keep
14	the value OUT low and avoid false states before VINT
15	is powered up?
16	MR. ANDERSON: Objection. Form.
17	THE WITNESS: I don't think you can talk
18	about false states before VINT is powered up. I
19	think you would have to power the circuit up before
20	you could actually look at the state of the circuit.
21	BY MR. JONES:
22	Q. Okay. So if VINT is powered up and the
23	fuse had been programmed, meaning blown, does the
24	diode then prevent OUT from taking high state?
25	A. No, not exactly. The diode is going to

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limit the output voltage to the internal power supply
voltage VINT plus the diode's threshold voltage.
So with the circuit powered up, the diode
would still allow OUT to go high if the fuse wasn't
blown.
I think what the diode is doing is bleeding
off extra charge on OUT when VINT is at ground just
ensuring OUT starts up in a low voltage state.
But if the fuse isn't blown, then OUT can
go high just fine with the diode there, and the diode
won't limit the output voltage to a ground or a low
voltage.
Q. And why if I understood correctly, why
do you want OUT to be low, in a low voltage state,
before VINT starts ramping up?
A. Are we still focusing on the fuse being
blown or programmed?
Q. Yes.
<pre>Q. Yes. A. So when the fuse isn't blown, OUT is pulled</pre>
<pre>Q. Yes. A. So when the fuse isn't blown, OUT is pulled high to VINT. However, if for some reason out has</pre>
Q. Yes. A. So when the fuse isn't blown, OUT is pulled high to VINT. However, if for some reason out has some residual charge stored on it, the diode isn't
Q. Yes. A. So when the fuse isn't blown, OUT is pulled high to VINT. However, if for some reason out has some residual charge stored on it, the diode isn't there, the circuit could the OUT could be a high
Q. Yes. A. So when the fuse isn't blown, OUT is pulled high to VINT. However, if for some reason out has some residual charge stored on it, the diode isn't there, the circuit could the OUT could be a high voltage because of that residual charge, and the
Q. Yes. A. So when the fuse isn't blown, OUT is pulled high to VINT. However, if for some reason out has some residual charge stored on it, the diode isn't there, the circuit could the OUT could be a high voltage because of that residual charge, and the diode would using the diode would then allow the

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1	Q. Okay. And in that case, if there wasn't a
2	diode and there was enough residual charge on OUT to
3	be read as a high value, still in the condition where
4	the fuse is programmed, why is that bad?
5	A. Are we assuming that power hasn't been shut
6	off so that output charge can just drain to ground
7	through the off transistor 110, for example?
8	Q. Correct. Before that.
9	A. So if I understand correctly, if we program
10	the fuse F-1 power still applied, then there's no way
11	for the output to be pulled low because, for example,
12	there's been nothing actively pulling OUT down.
13	In fact, the diode would leak the output to
14	a high voltage, and the circuit would be the same or
15	operate the same as if the fuse hadn't been
16	programmed.
17	Q. And is that the specification called a
18	false state?
19	A. Can you point me to where it says "false
20	state" in the spec?
21	Q. Well, we can forego that.
22	A. Okay.
23	Q. That last question.
24	Just before that, you made a statement, and
25	hopefully this makes sense, it's kind of out of

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1	context, but what you said was are we assuming that
2	power hadn't been shut off so that output charge can
3	just drain to ground through the off transistor 110,
4	for example.
5	A. Yes.
6	Q. And can you explain to me what you meant by
7	that?
8	A. So if we look at Figure 2A, for example, if
9	the VINT is zero, and external Vcc is zero, and the
10	fuse is blown obviously, if the fuse isn't blown
11	then OUT gets shorted to VINT, which is zero. Then
12	if we have a charge on out, we have a leakage path
13	through 110, which will pull OUT to ground through
14	the leakage in 110. And of course, if we have the
15	diode, it will also get pulled out; it will also get
16	pulled to ground through the diode. But even without
17	the diode there, OUT will get pulled to ground
18	through transistor 110 and transistor 110.
19	Q. Just to clarify, at the end of that answer
20	you said the diode there OUT will get pulled to
21	ground with transistor 110 and transistor 110?
22	A. Just transistor 110.
23	Q. Will okay. If VINT is powered up, will
24	the voltage on OUT get pulled to ground through
25	transistor 110?

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1	MR. ANDERSON: Objection. Form.
2	THE WITNESS: If VINT is powered up and OUT
3	is high, then OUT will stay high. If VINT is powered
4	up and OUT is low, then OUT will stay low.
5	BY MR. JONES:
6	Q. And in that answer, are you assuming that
7	the fuse has been programmed?
8	A. Yes. Because if the fuse hasn't been
9	programmed, there's a short from V OUT to VINT.
10	Q. And out will necessarily follow VINT in
11	that case?
12	A. When it's shorted through the fuse, yes.
13	Q. So still related to this discussion, I
14	would like to talk about claim 1, column 8. There is
15	an element, the third element that reads a terminal
16	T1. Do you see that element?
17	A. Yes.
18	Q. And I would like to ask first what your
19	understanding of this language is in the context of
20	Figure 2A: A terminal T1 for providing a signal
21	indicating a state of the programmable latch.
22	A. So terminal T1, my understanding is that
23	would be OUT in Figure 2A. Terminal T1.
24	Q. Okay. And what does the language "a state
25	of the programmable latch" mean?

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1	А.	The state of the	e programmable latch
2	indicates	whether the fuse	e is blown or not blown. So
3	if OUT is	a 1 or a zero.	
4	Q.	So if the fuse i	s not blown, then OUT
5	should be	high, right?	
6	A.	Yes.	
7	Q.	And if the fuse	is blown, then OUT should
8	be low, r	ight?	
9		MR. ANDERSON: C	bjection. Form.
10		THE WITNESS: If	everything is working
11	right, yes	5.	
12	BY MR. JOI	NES:	
13	Q.	And I thought pr	eviously when we set up the
14	condition	that the fuse is	programmed and VINT was
15	powered up	p, if OUT is high	, then it will stay in that
16	state; is	that correct?	
17	А.	Can you repeat t	he first part of that
18	question?		
19	Q.	Sure. If the fu	se is programmed and VINT
20	is powered	l up, then if OUI	' is high, it will stay in
21	the high a	state?	
22	A.	If the circuit i	s malfunctioning, yes,
23	that's what	at will happen.	
24	Q.	Okay. What show	ld happen if the fuse is
25	programmed	d and VINT is pow	vered up, what state should

1	OUT be?
2	A. If the fuse is blown or programmed, then
3	OUT should go to a zero if things are working right.
4	Q. And if OUT doesn't go to a zero, then this
5	claim element is not met, right? Because the
6	terminal T1 does not provide a signal indicating a
7	state of the programmable latch?
8	MR. ANDERSON: Objection. Form.
9	BY MR. JONES:
10	Q. Right?
11	A. If OUT stays high independent of the fuse,
12	then the circuit isn't working correctly.
13	However, the language of the claim says
14	that the T1 is the signal indicating the state of the
15	programmable latch. If the programmable latch is
16	high, I don't know if I would say that the claim
17	element is not being met because all we need to do is
18	show that T1 indicates the state of the latch.
19	Now, if the state of the latch doesn't
20	represent the state of the fuse, whether it's been
21	blown or not, I don't think I think the claim
22	element will still be met because it requires
23	terminal T1 to provide a signal indicating to state
24	the programmable latch. I think there's more to I
25	mean, I think you're asking something a little

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1	different.
2	Q. I think I understand the point you're
3	making.
4	A. Okay.
5	Q. Let me ask a different question, then. If
6	the fuse is programmed and OUT is high, then that
7	terminal T1 OUT does not indicate the state of the
8	fuse; is that correct?
9	MR. ANDERSON: Objection. Form.
10	THE WITNESS: I think that's correct.
11	Terminal T1 would indicate the state of the latch in
12	that case, not the state of the fuse.
13	BY MR. JONES:
14	Q. And I mean, regardless of how the circuit
15	operates or what condition you're in, meaning whether
16	the fuse is programmed or not or VINT is powered up
17	or not, regardless of any of those conditions, your
18	understanding of this claim element is that terminal
19	T1 always indicates the state of the programmable
20	latch?
21	MR. ANDERSON: Objection. Form.
22	BY MR. JONES:
23	Q. Is that right?
24	A. I would have to qualify that with the other
25	parts of the claim that says a first terminal for

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1	receiving a first voltage, a second terminal for
2	receiving a second voltage.
3	If, for example, the first terminal
4	received ground and the second terminal received
5	ground, then terminal T1 wouldn't be providing a
6	signal indicating a state of the programmable latch
7	because there's no power going to the latch.
8	So to the extent that the latch is powered
9	up and were meeting the earlier claim elements, then
10	yes, terminal T1 provides a signal indicating the
11	state of the latch.
12	Q. Okay. So I would like to shift gears a
13	little bit to the next element, which is a
14	programmable electrical path, including a nonvolatile
15	programmable element.
16	Is this element generally. We're
17	talking about the fuse, right, in Figure 2A?
18	A. Just in general? Because there's
19	additional discussion in Column 7. But in general, I
20	think that it's referring to the fuse, yes.
21	Q. And sort of to start at the finish line
22	here and see how this goes, but in every embodiment
23	in the '492, the fuse is the only thing that
24	determines whether the terminal T1 is connected to
25	the first terminal or not; is that correct?

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1	MR. ANDERSON: Objection. Form.
2	THE WITNESS: I don't think that's exactly
3	correct if we look at column 7, lines 24 through 36.
4	But F1 is what determines if the terminal T1 connects
5	to the first terminal, and we can call F1 the
6	programmable path.
7	So I think loosely speaking that the
8	programmable path connects terminal T1 to the first
9	terminal, yes.
10	BY MR. JONES:
11	Q. And F1 is the only thing that determines
12	whether T1 connects to the first terminal or not,
13	right?
14	A. In the embodiment of Figure 2A, yes.
15	Q. Is there any other embodiment anywhere in
16	the patent where that is not true?
17	A. In Figure 8, F1 connects OUT to VINT if
18	it's not blown. In figure 7, F1 connects OUT to
19	VINT, or 212 if F1 is not blown.
20	Same thing in Figure 6 and Figure 2A, yes.
21	Q. So there are no embodiments well, let me
22	strike that and try to just ask you the same thing
23	again. I apologize.
24	F1 in every embodiment in the patent is the
25	only thing that determines whether T1 connects to the

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1	first terminal or not, right?
2	MR. ANDERSON: Objection. Form.
3	THE WITNESS: If I understand what you're
4	saying, yes, F1 determines if the OUT or terminal 1
5	is connected to the internal power supply voltage
6	212, neglecting, though, leakage through the diode
7	that's added, for example, in parallel with the fuse
8	F1.
9	BY MR. JONES:
10	Q. And back to Claim 1 here at line 46 to 50,
11	does that claim term require that the nonvolatile
12	programmable element be the only thing that connects
13	T1 to the first terminal?
14	MR. ANDERSON: Objection. Form.
15	THE WITNESS: No, it doesn't require that's
16	the only thing.
17	BY MR. JONES:
18	Q. Okay. If there were in a hypothetical
19	here, if there were another fuse in series with the
20	first, then and let's say that other fuse was
21	programmed.
22	A. Okay.
23	Q. If the first fuse was not programmed,
24	meaning it was conductive, but again, the other fuse
25	is programmed, then the terminal T1 does not connect

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1	to the first terminal, right?	
2	A. If there are two fuses in the series, and	
3	one of the fuses is blown, then if the two fuses are	
4	between the internal voltage and OUT, having one of	
5	the blown fuses would not allow a connection through	
б	the fuses between VINT and OUT.	
7	Q. And in that case, this claim element would	
8	not be met; isn't that right?	
9	A. So are we redefining programmable element	
10	to be the series connection of two fuses?	

Q. No. I'm still just defining it as theoriginal when I called it the first fuse.

A. I don't know. That doesn't make any sense
because when one fuse is blown, it doesn't do -- I
mean, it's no different than if you have two fuses
blown. And so I would need to think about that.

But -- yeah, I would need to think about it. I didn't form an opinion on having two fuses in a series.

20 Q. I'm going to hand you the Joo reference, 21 this discussion, if we just jump right into it.

So that's Exhibit 1010.

(Exhibit 1010 was marked for

identification.)

25

22

23

24

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1	BY MR. JONES:
2	Q. And I see you're opening one of your
3	declarations. I assume the declaration will lead to
4	the Joo discussion, which will be in the 781 IPR.
5	A. Correct.
6	Q. Okay. Now, is it your opinion that in Joo
7	Figure 2, fuse 2 meets the claim element that we were
8	just talking about, the programmable electrical path
9	nonvolatile programmable element?
10	MR. ANDERSON: Objection. Form.
11	THE WITNESS: Yes, I discuss that starting
12	on page 45 of my declaration, the one concerning Joo.
13	BY MR. JONES:
14	Q. Now, in Joo Figure 2, if MP1 were
15	nonconductive, then the first terminal is necessarily
16	not connected to the terminal T1, right?
17	MR. ANDERSON: Objection. Form.
18	THE WITNESS: If the fuse, fuse 2 in Joo
19	Figure 2 is not blown, is not programmed, then
20	terminal T1 is connected to the first terminal. Here
21	Vcc, Figure 2 of Joo, through the variable impedance
22	electrical path MP1. So I don't think I would agree
23	with that because MP1 is not a fuse or something that
24	can be blown.
25	

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1	BY MR. JONES:
2	Q. What if the signal FENB were high?
3	A. Then the impedance of MP1 would be high.
4	But as discussed in the '492 transistor is a variable
5	impedance electrical path, so I still think that
6	terminal T1 would be connected to the first terminal,
7	Vcc, as long as fuse 2 is not blown.
8	Q. So is it your opinion that if FENB was a
9	high value, that a current flows across MP1?
10	A. MP1 would have a high impedance, and as
11	long as there's a potential across MP1, even if FENB
12	were high, then there would be a current flowing
13	through MP1 called the off current.
14	Q. But under that condition you would say that
15	MP is off, right?
16	A. It would have a high variable impedance.
17	It would have a high impedance, yes, so it would be
18	from transistor point of view off.
19	Q. So I would like to look at claim 2 in the
20	'492 patent. It says I'll wait a second for you
21	to find your spot in the declaration.
22	A. Okay. Thank you.
23	Q. Claim 2 says, "Wherein, during operation of
24	the latch." Do you have any opinion about what that
25	means? What does it mean to be during operation of

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1	the latch?
2	A. I mean, just at a high level, the
3	operation of the latch during operation means that
4	you've powered up the latch, so you've applied the
5	first and second voltages that are talked about in
6	claim 1.
7	Q. Okay. So on that point, claim 1 is an
8	apparatus claim, right?
9	A. Yes.
10	Q. And so is it your understanding that the
11	limitations in claim 1 only needs to be met when the
12	voltages are applied? Or is it your understanding
13	that to meet all the elements of claim 1, a structure
14	must always have the claim language?
15	MR. ANDERSON: Objection. Form.
16	THE WITNESS: For claim 1 alone, my
17	understanding is that the apparatus has to have at
18	least the claimed elements, such as a first terminal
19	4 receiving a first voltage, terminal T1 for
20	providing a signal, et cetera.
21	However, in claim 2 it says the
22	programmable latch of claim 1 wherein during
23	operation of the latch. And I take operation of the
24	latch to mean that the apparatus is being used, not
25	just simply present.

R. Jacob Baker, Ph.D., P.E. Samsung Electronics vs. Promos Technologies BY MR. JONES: 1 So back in claim 1, though, claim 1 2 0. Okav. 3 doesn't say wherein during operation of the latch, 4 right? I don't see that, correct. 5 Α. 6 And so the elements in claim 1 have to be 0. 7 present regardless of whether you're operating the 8 latch or not; isn't that right? 9 For claim 1, yes. Α. 10 And so isn't it true that the language of ο. claim 1 needs to be met even if you're not applying a 11 12 first and second voltage? 13 For claim 1, it simply requires, for Α. 14 example, a first terminal for receiving a first voltage, a second terminal for receiving a second 15 16 voltage. So it doesn't need to be operating, 17 correct. It's an apparatus claim. 18 Okay. I'm going to turn to the McAdams Ο. 19 reference. So do you want a short break? Yes, please. 20 Α. 21 (A recess was taken from 9:54 a.m. 22 to 9:59 a.m.) BY MR. JONES: 23 So I would like to hand you the McAdams 24 ο. 25 reference, 1006.

R. Jacob Baker, Ph.D., P.E. Samsung Electronics vs. Promos Technologies (Exhibit 1006 was identified.) 1 2 BY MR. JONES: Are you familiar with this reference, 3 0. 4 Dr. Baker? 5 Α. Yes. 6 ο. I would like to start in column 2, around 7 line 21. 8 Α. Okay. 9 And ask you if this paragraph here, ο. McAdams, is talking about the same -- the same 10 condition that the '492 background talked about? 11 12 MR. ANDERSON: Objection. Form. 13 THE WITNESS: There's some discussion in 14 column 1 of the '492 about -- roughly at lines 39 on about OUT may tend to have a potential raise to lodge 15 a level 1. I think in general the discussions are 16 similar. I don't think they're exactly the same. 17 BY MR. JONES: 18 19 Well, McAdams is also talking about 0. capacitive coupling to node 14; isn't that right? 20 21 Α. Yes. It says in line 27, column 2 of 22 McAdams, "Any capacitive coupling of voltage to node 14 from the Vcc transition is quickly discharged." 23 24 And where is it discharged in Figure 1 of Q. McAdams? 25

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1	Α.	It's discharged through transistor 11.
2	Q.	And that's an NMOS transistor, right?
3	Α.	Transistor 11 is NMOS, yes.
4	Q.	And the other of strike that again.
5		Is node 14 the drain or the source of NMOS
6	11?	
7	Α.	The drain.
8	Q.	And the source is grounded, right?
9	Α.	Yes.
10	Q.	And the transistor is off in this
11	condition;	is that right?
12		MR. ANDERSON: Objection. Form.
13		THE WITNESS: I don't follow which
14	condition.	
15	BY MR. JON	ES:
16	Q.	The paragraph in column 2 that we're
17	talking ab	out with node 14 having excess charge and
18	dissipatin	g through transistor 11, does that occur
19	when trans	istor 11 is on or off?
20		MR. ANDERSON: Objection. Form.
21		THE WITNESS: My understanding is the
22	situation	described in column 2, lines 21 through 34
23	of McAdams	, the transistor 11 is on.
24	BY MR. JON	ES:
25	Q.	Okay. And then there's a discussion that

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1	goes from line 29 to 34 about the coupling to node 14
2	closely tracking Vcc.
3	Is that discussion a condition when
4	transistor 11 is on or off?
5	A. That discussion is talking about how if the
6	fuse is blown and Vcc rises quickly, coupling to node
7	14, that node 14 will eventually get pulled low
8	through transistor 11 due to leakage, and that will
9	in turn, although not discussed there, turn on
10	transistor 11 so the transistor 11 is on.
11	Q. So I'm looking at Figure 2A of the '492
12	patent.
13	A. Okay.
14	Q. Wouldn't the same be true here? In other
15	words, if the fuse were blown and VINT rose quickly
16	and caused capacitive coupling on OUT, wouldn't that
17	dissipate through transistor 110 to ground?
18	A. There will be leakage through transistor
19	110, just like in McAdams.
20	However, in Figure 2A of the '492, you also
21	have a diode. And if the diode leakage is greater
22	than the transistor leakage 110, then the diode will
23	keep leakage through the diode, will keep OUT high.
24	And so it's a little bit different than what's
25	described in McAdams, because in McAdams you don't

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1	have that extra leakage path up through the diode
2	that you have in Figure 2A of the '492.
3	Q. Let's talk about Figure 1, then, of the
4	'492. If there's capacitive coupling on OUT, then
5	wouldn't that dissipate across transistor 110 to
6	ground, like McAdams described?
7	MR. ANDERSON: Objection. Form.
8	THE WITNESS: OUT will be pulled to ground
9	through 110 if fuse 1 is programmed or blown because
10	of the leakage through 110, yes, over time.
11	BY MR. JONES:
12	Q. Does that contradict what the inventors of
13	the '492 said in columns 1 and 2?
14	MR. ANDERSON: Objection. Form.
15	BY MR. JONES:
16	Q. And specifically, column 1 from line 40.
17	A. In column 1 of the '492 in line 40 or so,
18	they're not focusing or discussing the leakage
19	through transistor 110, which would discharge OUT to
20	ground if fuse F1 were blown.
21	Q. When I read these two references together,
22	it seems that both McAdams and the '492 are
23	recognizing the exact same condition, that being that
24	there's capacitive coupling on a node when the fuse
25	is blown

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1	But McAdams is saying don't worry about it,
2	it will dissipate across the NMOS, whereas the '492
3	says this is a big problem, we need to solve this
4	problem.
5	Is that a correct understanding of these
6	two references?
7	MR. ANDERSON: Objection. Form.
8	THE WITNESS: The '492 is neglecting the
9	leakage through transistor 110, which will pull out
10	to ground in Figure 1 of the prior art. The McAdams
11	reference is not neglecting that leakage current.
12	It's stating what will happen is that OUT will be
13	pulled to ground through transistor 11 in Figure 1,
14	which corresponds to transistor 110; figure 1 of the
15	'492.
16	In the '492, they've added the diode, which
17	will not only increase the capacitive coupling from
18	the internal power supply to OUT, but will also
19	provide a leakage path that pulls OUT up. That one
20	doesn't have a McAdams or Figure 1 of the prior art,
21	and that leakage path, if it's especially if it's
22	leaking greater than the leaking through transistor
23	110 in Figure 2A, could keep the output voltage high,
24	which wouldn't be a problem in Figure 1 of the prior
25	art, the '492 or Figure 1 of McAdams.

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1	BY MR. JONES:
2	Q. Is it true that both McAdams and the '492
3	are describing the same condition?
4	MR. ANDERSON: Objection. Form.
5	THE WITNESS: Are you talking about when
6	they describe the capacitive coupling from Vdd to the
7	other side of the fuse?
8	BY MR. JONES:
9	Q. Yes.
10	A. They both describe them when Vdd powers up
11	that there will be capacitive coupling across the
12	fuse, yes.
13	Q. But McAdams in column 2 says that's not a
13 14	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across
13 14 15	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across transistor 11, right?
13 14 15 16	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across transistor 11, right? MR. ANDERSON: Objection. Form.
13 14 15 16 17	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across transistor 11, right? MR. ANDERSON: Objection. Form. THE WITNESS: McAdams points out that the
13 14 15 16 17 18	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across transistor 11, right? MR. ANDERSON: Objection. Form. THE WITNESS: McAdams points out that the transistor will pull node 14, the bottom side of the
13 14 15 16 17 18 19	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across transistor 11, right? MR. ANDERSON: Objection. Form. THE WITNESS: McAdams points out that the transistor will pull node 14, the bottom side of the fuse, to ground because transistor 11 leaks. And in
13 14 15 16 17 18 19 20	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across transistor 11, right? MR. ANDERSON: Objection. Form. THE WITNESS: McAdams points out that the transistor will pull node 14, the bottom side of the fuse, to ground because transistor 11 leaks. And in '492, they failed to point out that transistor 110
13 14 15 16 17 18 19 20 21	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across transistor 11, right? MR. ANDERSON: Objection. Form. THE WITNESS: McAdams points out that the transistor will pull node 14, the bottom side of the fuse, to ground because transistor 11 leaks. And in '492, they failed to point out that transistor 110 well, at least in the section we're focusing on, will
13 14 15 16 17 18 19 20 21 22	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across transistor 11, right? MR. ANDERSON: Objection. Form. THE WITNESS: McAdams points out that the transistor will pull node 14, the bottom side of the fuse, to ground because transistor 11 leaks. And in '492, they failed to point out that transistor 110 well, at least in the section we're focusing on, will also leak and pull output the output to ground in
13 14 15 16 17 18 19 20 21 22 23	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across transistor 11, right? MR. ANDERSON: Objection. Form. THE WITNESS: McAdams points out that the transistor will pull node 14, the bottom side of the fuse, to ground because transistor 11 leaks. And in '492, they failed to point out that transistor 110 well, at least in the section we're focusing on, will also leak and pull output the output to ground in the prior art.
13 14 15 16 17 18 19 20 21 22 23 24	Q. But McAdams in column 2 says that's not a problem because that charge will dissipate across transistor 11, right? MR. ANDERSON: Objection. Form. THE WITNESS: McAdams points out that the transistor will pull node 14, the bottom side of the fuse, to ground because transistor 11 leaks. And in '492, they failed to point out that transistor 110 well, at least in the section we're focusing on, will also leak and pull output the output to ground in the prior art. BY MR. JONES:

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1	few places in the spec that talk about embodiments
2	with no diode. And one of those places, for example,
3	is at column 2, line 38.
4	Can you describe what would happen in this
5	embodiment with no diode if there were capacitive
6	coupling at node at the output node?
7	A. So
8	MR. ANDERSON: Objection. Form.
9	THE WITNESS: Well, what's described there
10	in column 2 of the '492, some embodiments with only
11	one CMOS inverter and no capacitor operates
12	successfully even without a diode is exactly what's
13	seen in Figure 1 of McAdams, and as discussed in
14	McAdams the reason it operates successfully is since
15	there's no diode providing a leakage path up to the
16	power supply, that transistor 11 in McAdams or
17	transistor 110 in the '492 will provide a leakage
18	path pulling that node to ground and will get the
19	correct output.
20	BY MR. JONES:
21	Q. And that leakage current will only pull the
22	node to ground if the power is not turned on; is that
23	right?
24	A. No. It will always pull the node 14 and
25	346 to ground when the fuse is programmed or blown,

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1	as it will in Figure 1 of the '492 or Figure 2A of
2	the '492 without the diode because there's no other
3	path for the output or no other path for pulling that
4	bottom side of the fuse up.
5	Q. So in the '492, column 2, line 47, it says
6	specifically that the power is turned off after
7	programming and the voltage on OUT is allowed to
8	return to ground.
9	And I'm paraphrasing that, but why do they
10	make the point that power is turned off in this
11	discussion?
12	MR. ANDERSON: Objection. Form.
13	THE WITNESS: Again, the patent seems to
14	neglect the leakage through transistor 110. And in
15	the embodiment discussed in that paragraph of using
16	one inverter and no diode, which is Figure 1 of
17	McAdams, if you don't recognize that transistor 110
18	leaks, then this is saying because it apparently
19	doesn't recognize that transistor 110 leaks that
20	it still doesn't matter because you're going to shut
21	the power off after programming, and so OUT will
22	start out as a zero.
23	BY MR. JONES:
24	Q. In that state when power is not on, if you
25	do not account for the leakage across 110, where does

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1	any excess charge on the OUT node go?
2	A. Well, ultimately it will just drain to the
3	substrate and cause the voltage on the OUT node to go
4	to zero when there's no power applied.
5	Q. In the '492 at column 5, from line 51, are
6	they talking about the same embodiment that we just
7	talked about?
8	A. So this is this paragraph is talking
9	about Figures 2A and 6. And Figure 6 is the same as
10	Figure 1 of McAdams except Figure 6 adds a diode.
11	And in column 5 the discussion is that if
12	the diode is omitted, that because power is turned
13	off, the output will go to ground, that the diode may
14	be omitted. And so things would still work okay.
15	It's basically just repeating what's
16	already taught in McAdams with the difference that
17	McAdams teaches that we know they leak to ground
18	through transistor 11, which is equivalent to
19	transistor 110 in the '492, even if you don't have
20	the power shut off.
21	Q. So looking in '492, claims 1 and 14,
22	they're the only two independent claims, both
23	apparatus claims. And much of the language is
24	identical. But I'll say one difference is that claim
25	14 does not claim a diode, right?

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1	A. A diode is not claimed in 14, correct.			
2	Q. And in claim 1 a diode is claimed, right?			
3	A. Correct. Claim 1 has a diode. Claim 14			
4	may have a diode, but it's not required.			
5	Q. Now, do you think that claim 14 is claiming			
6	the embodiment, for example, in column 5 from line 51			
7	that we just talked about?			
8	MR. ANDERSON: Objection. Form.			
9	THE WITNESS: I haven't done an analysis on			
10	that. I think it could be. But again, there could			
11	be a diode present in claim in the apparatus that			
12	practices claim 14.			
13	I mean, if you look at Figure 6 or Figure			
14	8, which have similar topography, just different			
15	polarity to power supplies. But if you look at			
16	Figure 6, for example, I think Figure 6 would be an			
17	embodiment that practices claim 14. And in that			
18	embodiment, there is a diode, even though it's not			
19	claimed.			
20	BY MR. JONES:			
21	Q. Going back to McAdams.			
22	A. Okay.			
23	Q. I understood a prior answer of yours to be			
24	that McAdams recognizes that charge on node 14 will			
25	leak to ground through transistor 11 even if power is			
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1	on; is that correct?			
2	A. Yes.			
3	Q. Does McAdams teach at all that if power is			
4	off, a charge will make it across transistor 11?			
5	A. Are you asking if McAdams teaches that if			
б	power is off, that a node in the circuit will			
7	discharge to ground?			
8	Q. Yes.			
9	A. I don't recall McAdams teaching that. But			
10	that's something that a person of ordinary skill, or			
11	I guess common sense would understand that if there's			
12	no source of power connected to a circuit, over time			
13	the charge or energy stored in the circuit will drain			
14	to ground and go to everything in the circuit will			
15	go to ground state.			
16	So I guess I'm not entirely I kind of			
17	wouldn't expect them to talk that if there's no power			
18	applied to the circuit, that the circuit relaxes to			
19	the ground state.			
20	Q. To be more precise about that question,			
21	does McAdams teach that power will dissipate across			
22	transistor 11 specifically when power is off?			
23	A. Transistor 11 will continue to leak even if			
24	power is removed from the circuit, and I don't recall			
25	McAdams teaching that.			

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1	Q. Okay. I would like to move on to the Uda				
2	reference, which is Exhibit 1007.				
3	(Exhibit 1007 was identified.)				
4	BY MR. JONES:				
5	Q. Focusing first on Figures 5 and 6.				
6	A. Okay.				
7	Q. Is it your understanding that Figure 6				
8	relates to Figure 5 in some way? And you may refer				
9	to like columns 9 and 10, 11 roughly.				
10	A. Figure 5 is the circuit diagram showing the				
11	fuse arrangement of Figure 2. And then Figure 6 is a				
12	cross section of the fuse arrangement of Figure 2,				
13	yes.				
14	Q. And are you familiar with the term ECL				
15	logic, emitter coupled logic?				
16	A. Yes.				
17	Q. What does that term describe?				
18	A. It's a type of logic implemented using				
19	bipolar junction transistors that was first created,				
20	if I remember correctly, in the late 60s. The output				
21	logic swings from roughly minus .8 to minus 1.5.				
22	Q. Are figures I should say is Figure 6 ECL				
23	logic?				
24	A. No. Figure 6 is a cross-sectional view.				
25	And I don't see any transistors that would be used to				

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1	implement ECL logic or emitter coupled logic in			
2	Figure 6.			
3	Q. Does it make sense to talk about a			
4	fabrication process using ECL design?			
5	MR. ANDERSON: Objection. Form.			
6	THE WITNESS: It makes sense to talk about			
7	a fabrication process used to implement ECL, yes.			
8	BY MR. JONES:			
9	Q. And I assume you're familiar with the			
10	concept of CMOS as well, right?			
11	A. Yes.			
12	Q. And can you tell by looking at Figure 6 if			
13	this was made using a process that could also			
14	implement ECL or CMOS?			
15	MR. ANDERSON: Objection. Form.			
16	THE WITNESS: I haven't formed an opinion			
17	on that. But just sitting here right now, I think			
18	that the answer is yes. These metal layers and			
19	interconnect could be used in either a CMOS or a			
20	bipolar process that implements ECL.			
21	BY MR. JONES:			
22	Q. So you could design a CMOS transistor in			
23	this cross section of Figure 6?			
24	MR. ANDERSON: Objection. Form.			
25	THE WITNESS: Again, I haven't studied that			

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1	in detail, but I think the answer is yes, because			
2	what's being shown here in Figure 6 and the			
3	interconnect layers and fuses and such corresponding			
4	to Figure 5.			
5	And the wires in a CMOS process, metal			
6	interconnect layers I say wires, but the metal			
7	interconnect layers are the same as in a are the			
8	same between CMOS and ECL in general.			
9	BY MR. JONES:			
10	Q. Figure 6 also has layers 18, 19 and 20,			
11	which are not interconnect layers, right?			
12	A. 18, for example, is a semi-conductor			
13	substrate. And that is not an interconnect layer.			
14	And both CMOS and ECL technology utilize a			
15	semi-conductor substrate.			
16	Let me look at 19, which I think is the			
17	other one you mentioned. And 19 is a buried layer of			
18	doping. It looks like just a doping layer, and			
19	that's common in both types of fabrication processes.			
20	And 20 is an epitaxial layer, and that's			
21	also common in both types of logic processes.			
22	So I think that it's reasonable that this			
23	cross-sectional view could be from a CMOS or a			
24	bipolar process. I haven't studied it in detail, but			
25	just looking at the cross-sectional view, I think it			

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1	could be for either type of process.			
2	Q. Now, where does Vee in Figure 5, where does			
3	that value connect in Figure 6?			
4	MR. ANDERSON: Objection. Form.			
5	THE WITNESS: I'm unsure. I would need to			
6	spend some time reviewing this. But just looking at			
7	it right here, if I had to point to something that I			
8	think it might be where the Vee is connected in			
9	Figure 6, I would point to 27A2. But I'm unsure.			
10	But I can spend more time and read and see			
11	if it's clear in the spec, but I think it would be			
12	27A2.			
13	And the reason I say that is if you look at			
14	the metal connection 27A2, 26A2, that's connected now			
15	to what looks like a highly doped area, 22A, which			
16	goes over to what they have as a resistor. And I			
17	think that that would likely be the resistor in			
18	Figure 5.			
19	And the connection to the resistor on the			
20	right side shows it goes up through the metal stack.			
21	But again, I'm unsure. I would need to spend some			
22	time looking at that. That's not something I formed			
23	an opinion on.			
24	BY MR. JONES:			
25	Q. Can you tell the resistor symbol that's			

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1	drawn, whether that corresponds with R1 or R2 of			
2	Figure 5?			
3	A. I don't know. I'm unsure even if that's			
4	the one going to Vee, or if that's the one going to			
5	the gate of 17.			
6	And I scanned the specification, and I			
7	didn't see anything jump out with a detailed			
8	specification there. But again, I haven't formed any			
9	opinion on this cross-sectional view and how it			
10	relates to Figure 6 in my declaration.			
11	Q. There's a symbol in Figure 5. Let's just			
12	look at R2, for example. There's R2 is drawn as a			
13	resistor. And then there's a horizontal line above			
14	it going up to V2 and ground.			
15	A. Yep.			
16	Q. What is that symbol there? It's a resistor			
17	with a horizontal line over it, what is that			
18	representing?			
19	A. That indicates that the resistor was made			
20	with an implanted or diffused semi-conductor			
21	material.			
22	So in this case, the flat line corresponds			
23	to P-type material. So the resistor R2, for example,			
24	would be N-type material.			
25	And so as you change the voltage on the			

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1	resistor R2, you change the this is going to sound				
2	technical, but you change the width of the depletion				
3	region between the N-type material that's used to				
4	implement R2 and the P-type material adjacent to that				
5	N-type material. So the resistance changes.				
6	That P-type material is also used for the				
7	anode of diode 2.				
8	But in real simple terms, it just means				
9	that R2 is implemented with a semi-conductor				
10	material, and then its value will change with the				
11	voltage applied across it.				
12	Q. And if resistor R2 is the resistor shown in				
13	Figure 6 I want you to assume that.				
14	A. Okay.				
15	Q. Then where is diode D2 in Figure 6?				
16	A. Again, I haven't looked at this in detail.				
17	But just looking at that and making that assumption,				
18	material 20 would be N-type material. Material 19				
19	would be P-type material. So the diode would be				
20	between material 20 and 19.				
21	Now, again I haven't looked at that, so it				
22	may between material 19 and material 18.				
23	So for example, if material 18 were N-type,				
24	then material 19 and 20 could be P-type. And that				
25	would be the connection, would be a P-type material				

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1	would be the diode.			
2	And so instead of having R2 as N-type, it			
3	would simply be P-type, and then the other side of			
4	diode D2 would be 18 or ground.			
5	Again, I haven't looked at the specifics of			
6	this, but I've looked at enough cross-sectional areas			
7	to know generally what things are.			
8	So that would mean R2 would be a P-type			
9	resistor, and substrate would be N-type.			
10	And if you want me to be more exact, I can			
11	go read the specification and find out what the real			
12	answer is.			
13	Q. I think what I'm interested in here is how			
14	D2 connects to node T in Figure 6. So do we know			
15	I guess I haven't asked this, but do you know where			
16	node T is in Figure 6?			
17	A. I don't know what the correspondence			
18	between Figure 6 and Figure 5 is. For example,			
19	Figure 5 shows two resistors.			
20	And I see one resistor symbol there. I			
21	think Figure 6 is just a representative			
22	cross-sectional view of the semi-conductor process.			
	cross sectional view of the semi conductor process.			
23	I don't think it necessarily directly corresponds to			
23 24	I don't think it necessarily directly corresponds to Figure 5.			

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1	with that symbol there, do we know that the anode of			
2	diode D2 is not connected to node T directly?			
3	A. Well, I think it could be. So if R2 is a			
4	P-type material, and that P-type material was the			
5	anode of D2, then it would be directly connected to			
б	T. And then the N-type material, which is the			
7	cathode of D2, would be connected to ground.			
8	Q. So in column 10 we may need to dig in, a			
9	little bit at least, of details here. 10 line 20, it			
10	says the substrate 18 is made of a P-type silicon			
11	single crystal.			
12	A. Okay.			
13	Q. And you can read maybe the rest of that			
14	paragraph. But from that, going back to Figure 6,			
15	can you tell, I guess, where the anode of D2 is?			
16	MR. ANDERSON: Objection. Form.			
17	THE WITNESS: If 18 is a P-type material,			
18	and again, we're assuming the resistor seen in			
19	Figure 6 is the resistor R2 in Figure 5, then 20,			
20	layer 20 may be P-type. Layer 19 would be N-type.			
21	And then layer 19 would be connected to			
22	ground form so the diode D2 is formed between P-type			
23	layer 20 and N-type layer 19. Again, assuming that			
24	the resistor symbol seen in Figure 6 is the resistor			
25	D2 in Figure 5.			

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1	I don't know if you want to spend more			
2	time. We can look at what specifically the layers 19			
3	and 20, what types they are, N or P.			
4	So if I look at column 10, it says layer 19			
5	as illustrated is N-type impurities. So that's			
6	exactly what I just said.			
7	And then column epitaxial layer 20 is			
8	P-type. Again, that's exactly what I just said			
9	guessing. But that's confirmed in column 10, lines			
10	20 through 22.			
11	BY MR. JONES:			
12	Q. So with that understanding, let me try			
13	again. But is the anode of D2 connected directly to			
14	node T?			
15	MR. ANDERSON: Objection. Form.			
16	THE WITNESS: Again, assuming that R2 is			
17	the resistor seen in Figure 6, then yes, the P-type			
18	material would be connected to node T. That would be			
19	material 20.			
20	And then 19 would be the cathode of diode			
21	D2, which would be connected to ground.			
22	BY MR. JONES:			
23	Q. In Figure 5, is the value of Vee a negative			
24	value?			
25	A. I believe it is. That's my understanding.			

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1	Vee is a negative value, but I don't see it specified			
2	in a specification with my quick glance.			
3	Q. Is Vee a signal notation that's commonly			
4	used for the negative voltage for ECL circuits?			
5	A. Yes.			
6	Q. And I think you said that typically			
7	operates in the range from negative .8 volts to			
8	negative 1.5 volts?			
9	A. No. Vee is a terminating voltage that's			
10	different than the logic swing voltages.			
11	So if memory serves, for 100k ECL VE is			
12	minus 2 and for 10k ECL VE is like minus 5. But it's			
13	been like 30 years since I've designed something with			
14	ECL.			
15	Q. Is that a term that's used in CMOS			
16	circuits?			
17	A. In CMOS only, no. In circuits interfacing			
18	CMOS and ECL, I would say could be.			
19	Q. Are you familiar with any major process			
20	today that uses ECL process? Semi-conductor process.			
21	A. I mean, there's foundries that fabricate			
22	the legacy ECL products. Fairchild is an example.			
23	Motorola had fabs that fabricate ECL. I haven't kept			
24	up on where they're doing the fabrication now. So I			
25	can't say right off the top of my head.			

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1	Q.	Okay.		
2	Α.	And when we get	a chance, can we take a	
3	break?			
4	Q.	Sure. Do you mi	nd if I finish off like two	
5	or three minutes?			
6	A.	Yes.		
7	Q.	Just say yes to	everything. That's a joke.	
8	Α.	Yes.		
9	Q.	I won't ask you	yeses or nos just because I	
10	said that	•		
11		Is it your under	standing that most of the	
12	major sem	i-conductor proce	esses being used today are	
13	done acco:	rding to CMOS pro	ocess?	
14	Α.	When you say	the language is a little	
15	awkward.	When you say be	ng used today, there's lots	
16	of foundr	ies that are fab	ricating chips that have	
17	been arou	nd for 30, 40 yea	ars.	
18		So are you talki	ng about like process	
19	development right now, or stuff that's already been			
20	around for	r a while?		
21	Q.	I meant new chip	os that are being made,	
22	designed a	and made today.	Not legacy production. Not	
23	legacy pro	oducts.		
24		MR. ANDERSON: (Dbjection. Form.	
25		THE WITNESS: Ir	general, it's CMOS.	
	1			

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1	That's more than 90 percent of what the technology is
2	used for chips. But there are still semi-conductor
3	processes being developed for niche markets, like
4	silicon carbide, gadolinium nitride, some high-speed
5	bipolar process that might implement ECL.
6	But the majority of the process technology
7	focuses on fine line CMOS.
8	MR. JONES: So let's break here. We'll
9	have to continue this a little bit, but we can stop
10	and then come back.
11	(A recess was taken from 11:04 a.m.
12	to 11:11 a.m.)
13	BY MR. JONES:
14	Q. I would like to basically just get a list
15	of differences between ECL and CMOS.
16	Are you comfortable just answering that, or
17	should I walk you through?
18	A. With the technology differences?
19	Q. Sure.
20	A. Okay. So CMOS uses MOS transistors, like
21	17 in Figure 5 of Uda.
22	ECL uses bipolar junction transistors. Let
23	me see if I can find one of those in Uda.
24	So for example, in Uda, Figure 58, Q3 and
25	Q4, are bipolar junction transistors.

R. Jacob Baker, Ph.D., P.E. Samsung Electronics vs. Promos Technologies And then QP1 and QP3, for example, are PMOS 1 2 transistors. And then MN5 and MN7 are NMOS transistors. 3 4 So if we have ECL only, we would only have 5 the bipolars. If we have CMOS only, we would only 6 have the NMOS and the PMOS transistors. 7 And if we have both, as in Uda in figure 8 58, we have both bipolar transistors, NMOS transistors, and PMOS transistors. 9 Okay. You mentioned, when you were talking 10 Q. about manufacturing of products in niche markets, I 11 12 think that ECL is typically faster than CMOS; is that 13 right? 14 MR. ANDERSON: Objection. Form. 15 THE WITNESS: Well, it was true 30 years 16 ago or so. I don't think that's true nowadays. 17 BY MR. JONES: 18 Is there a difference in the power Ο. 19 consumption between circuits implemented using ECL versus CMOS? 20 21 MR. ANDERSON: Objection. Form. 22 THE WITNESS: I can't answer that. Ιt depends on the application. 23 2.4 BY MR. JONES: 25 Looking at Figure 5 of Uda, Figure 5 has a 0.

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1	resistor R1. Can we turn to that.
2	A. Yes.
3	Q. And Vee, I think you said you understand to
4	be a negative voltage; is that right?
5	A. That's what I said, yes. I don't recall
6	seeing it discussed in the oh, it's there in
7	column 9 roughly, line 32, Vee with a negative
8	voltage of about minus 4 volts.
9	Q. Okay. And so whatever voltage exists on T,
10	it will be dissipated to Vee; is that right?
11	MR. ANDERSON: Objection. Form.
12	THE WITNESS: No. Can you give me a
13	specific example? Because if the power's off in the
14	circuit, then T, just like all voltages in the
15	circuit, will go to the resting or ground state.
16	Because that's the reference for voltage, is whether
17	it's positive or negative.
18	BY MR. JONES:
19	Q. So let me ask a little precise and
20	different question.
21	So if power is on in the circuit and the
22	fuse is not programmed, then resistor R1 will consume
23	power, right?
24	A. Yes. T will be shorted to ground through
25	fuse 16, Figure 5. And if Vee is nonzero, and R1 is

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1	not infinite, then R1 will consume power.
2	Q. Couldn't the designers of Figure 5,
3	couldn't they have designed R1 as an NMOS or some
4	sort of switch that would be a lower power consuming
5	edition of the same functionality?
6	MR. ANDERSON: Objection. Form.
7	THE WITNESS: I think the answer is no. Rl
8	is a terminating resistor used to transmit a
9	transmission line.
10	But let me look at the specification and
11	see how it describes R1 in Figure 5.
12	So if R1's resistance was made higher, then
13	it would dissipate less power, assuming everything
14	else is the same, with T being shorted to ground
15	through fuse 16 in Figure 5 of Uda.
16	BY MR. JONES:
17	Q. So let me make sure I understand the
18	relationship. The higher the resistance of R1 is,
19	the less power is consumed?
20	A. Assuming everything else is the same, yes.
21	Q. And the opposite is true, I assume?
22	A. Yes.
23	Q. I want to let me shift gears a little
24	bit. One thing on McAdams that I meant to ask
25	before do you have McAdams in front of you?

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1	A. Yes.
2	Q. In column 1, the second paragraph is, when
3	talking about the goals of the patent or the problem
4	that it solved. Can you describe those to me,
5	generally.
6	A. So in semi-conductor memory, when they're
7	fabricated, there will be faulty rows and/or columns
8	in the memory.
9	And so what's done to ensure that the
10	memory still functions with all bits working is to
11	swap out the faulty row and/or column with a
12	redundant row and/or column, and the way this is done
13	is by remapping the address that's applied to the
14	part to do the remapping, a fuse is used.
15	In the prior way of implementing the
16	circuitry to read out the state of the fuse, it talks
17	about, in the second paragraph, using, for example, a
18	long channel MOS transistor to minimize the current
19	through the fuse.
20	Another way it talks about is using a clock
21	to gate an MOS transistor so that the value of the
22	fuse is clocked in.
23	And then the way McAdams teaches is to use
24	a latch that will latch or represent the state of the
25	fuse and, thus, not need an external signal, like a

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1	clock, or dissipate any quiescent current as one
2	would get using a long L-transistor sensing the state
3	of the fuse.
4	Q. And doesn't it say that the one undesirable
5	result of the prior techniques at line 25 is that
6	they consume too much power?
7	A. It indicates that using the long
8	L-transistor or the external clock signal would
9	consume tens of micrograms of current. So that would
10	consume power, yes.
11	Q. And in fact, the next paragraph says it is
12	the principal object in the invention to reduce power
13	consumption, right?
14	A. Not precisely. But it says that the
15	principal objective of this invention is to improve
16	the performance by using less current so that the
17	stand-by power dissipation is lower.
18	Q. And McAdams is only teaching CMOS
19	circuitry, right?
20	A. Yes.
21	Q. Turning back to the '492 patent, claim 1,
22	the diode element.
23	A. Okay.
24	Q. There's some claim language which is a
25	predetermined range of values.

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1	A. Yes. The last element of claim 1.
2	Q. Yes. And what is your understanding of
3	what it means to be within a predetermined range of
4	values?
5	A. That the diode would limit the voltage on
6	the terminal T1 to within a diode drop of the voltage
7	on Vcc.
8	So for example, if the voltage on Vcc were
9	ground, then T1 would be limited to .7, whereas if
10	the voltage on Vcc was 5, then T1 would be limited to
11	5.6, 5.7.
12	Q. Now, I understand that it's your opinion
13	that the VAP would meet the claim element. But I'm
14	wondering about the breadth of this claim term,
15	predetermined range of values.
16	If there's, for example, a diode in series
17	with a resistor, then the value of the voltage on T1
18	would be more than the diode threshold lower than the
19	VINT; isn't that right?
20	MR. ANDERSON: Objection. Form.
21	THE WITNESS: I haven't formed an opinion
22	on using a resistor in series with a diode, but just
23	sitting here right now, I don't think that would
24	work.
25	I mean, if you look at column 3, work to

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1 meet the claim language, if you look at column 3, and 2 you look at the discussion around starting at the 3 paragraph on roughly line 33, talks about the PN 4 junction limiting the voltage on VINT to a threshold 5 voltage above -- I'm sorry, limiting the voltage on 6 T1 to a threshold voltage of VINT.

7 I think if you put a resistor in series
8 with a diode that when the current flows through the
9 resistor, then the voltage will change with the
10 current flowing in the resistor.

11 So I don't think that would meet the claim 12 language, but I haven't formed an opinion on that. 13 BY MR. JONES:

Q. I'm trying to understand your understanding
of this claim term, and whether it requires the
predetermined range of values to be precisely one
diode drop below the first voltage, or whether this
claim element is met for some other values other than
that one diode threshold drop.

20 MR. ANDERSON: Objection. Form.

21 THE WITNESS: The claim 13, for example, 22 talks about predetermined range consists of all 23 voltages below a predetermined value.

24If you put a resistor in series with a25diode, then the value is going to change with the

voltage drop across the resistor. 1 2 Whereas, if you use just a diode or some 3 other clamping element, or two diodes, for example, or three diodes, then the value will change. But it 4 5 will still be a predetermined value. 6 And then outside of that value, you're 7 limiting, or if you try to go outside that value, 8 you'll limit the node T1. 9 So I don't think it necessarily has to be implemented with one diode. But it has to be below 10 11 some value. The value can't be changing so that the 12 range changes. 13 BY MR. JONES: 14 Okay. So your point is that the upper end 0. of the range is a particular value that does not 15 16 change. But that upper value, that upper end of the range doesn't have to be exactly one diode threshold 17 18 below the first voltage? 19 MR. ANDERSON: Objection. Form. THE WITNESS: Well, kind of. I think, if 20 21 you want to be more precise, you could say that 22 the -- for example, the voltage on T1 needs to be one diode threshold below the power supply voltage. 23 But I think if you have two diodes there, that would meet 24 25 the claim language as well.

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1	But I think if you have a diode and a
2	resistor, it wouldn't meet the claim language because
3	then the upper bound would not be below a
4	predetermined value. Vcc plus .7, for example.
5	But variable depending on the resistance
6	and the current flowing through the resistance.
7	BY MR. JONES:
8	Q. And the same is true not just for resistor,
9	but for like a contact as well, right? That has an
10	inherent resistance to it, the voltage drop across
11	the contact would vary based on the current flowing
12	through it, right?
13	MR. ANDERSON: Objection. Form.
14	THE WITNESS: There might be a few
15	millivolts changed, but I don't think practically
16	that's an issue, because you could also argue that
17	wires have resistance.
18	And so there's a voltage drop across a
19	wire. I don't think that's really relevant, to be
20	honest.
21	BY MR. JONES:
22	Q. Okay. Let's talk about the Joo reference
23	again. I think I already gave it to you.
24	A. Yes.
25	Q. And these questions relate to your 781

R. Jacob Baker, Ph.D., P.E. Samsung Electronics vs. Promos Technologies 1 declaration. 2 Α. Okay. 3 Around page 56 of 120. 0. 4 Α. Okay. And then -- I'm looking across the table at 5 0. 6 you, I think -- I guess seeing that number it would 7 be page 53. 8 Α. Oh, sorry. Okay. 9 That would make more sense that way. Ο. 10 So are you familiar with the term "body 11 diode"? 12 Α. Yes. 13 What is a body diode? Q. 14 If we look at the figure 4.35 on page 56 or Α. 15 59 of 120. The body of the PMOS transistor is the N-well seen in that figure 4.35. And the body diode 16 would be the diode that's formed between that N-well, 17 or the body of the PMOS, and the P-substrate. 18 19 Is the body diode shown in schematic form Q. on this figure? 20 21 Α. Yes. 22 Which symbol is it? Q. 23 Α. It's the lowest diode on the right, just 24 slightly above and to the left of the P-substrate 25 label.

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1	Q. Okay. And it's flowing up, right? The
2	anode is on the bottom, the cathode is on the top for
3	the one that you're talking about, right?
4	A. Yes.
5	Q. And what's happening at that interface
6	between the N-well and the P-substrate that makes it
7	a diode?
8	A. There's a PN junction.
9	Q. Okay. I understand that makes it a diode.
10	But what's happening with the flow of electrons, or
11	physically that makes that a diode?
12	MR. ANDERSON: Objection. Form.
13	THE WITNESS: If the P-substrate becomes
14	more positive than the N-well, the diode that we're
15	talking about turns on and conducts current.
16	Whereas, if the N-well is at a higher
17	potential than the P-substrate, which is normal
18	operation, then the diode is reverse biased, and no
19	current flows.
20	BY MR. JONES:
21	Q. And you also have drawn above that diode we
22	just talked about, you've drawn two other diodes,
23	which are facing the other way between the source and
24	drain of a transistor and the N-well that they're in;
25	is that correct?

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A. Yes.
Q. Do you refer to those as body diodes?
A. One may refer to them as body diodes, but
generally they're referred to as the source body
diode or the drain body diode.
But I wouldn't be I mean, I don't think
it would be entirely incorrect to say it's a body
diode because the body is used as part of the diode.
Q. And at each of those interfaces, there's a
PN junction as well, right?
A. Yes.
Q. And that's why you say that each of those
interfaces creates a diode, right?
A. Yes.
Q. And on page well, three pages prior,
which is 56 of 120, you've drawn two diodes at the
interface between the source or drain and the body,
right?
A. Yes.
Q. Is that true for every PMOS transistor,
there's necessarily a source body diode and a drain
body diode?
A. Yes. And CMOS transistors, which are
fabricated in the bulk, or in a way for there has to
be a P plus N junction for the source and drain to

R. Jacob Baker, Ph.D., P.E. Samsung Electronics vs. Promos Technologies the body of the -- here the end substrate of the PMOS 1 2 device. Just more fundamentally, is every PN 3 Q. 4 junction a diode necessarily? 5 MR. ANDERSON: Objection. Form. 6 THE WITNESS: Yes. But if you give me some 7 example, I'll see if I can find some way that's not 8 true. But I think a PN junction is a diode, yes. BY MR. JONES: 9 Is there any other way to form a diode 10 Q. other than forming a PN junction? 11 12 Α. Yes. 13 Can you give me an example? Q. 14 Metal semi-conductor junction. Α. If the semi-conductor is lightly doped, it can form what's 15 16 called a Schottky or rectifying junction, which is a diode. 17 18 Looking at page 54 of 120. 0. 19 Α. Okay. I want to make sure I understand your 20 Q. 21 opinion. Is it your opinion that Joo alone teaches 22 this element, this diode element, at the top of this 23 page? To the extent that the PMOS transistor in 24 Α. 25 Joo is laid out to include the diode, then Joo could

1 teach it alone. 2 But I don't think that's clearly detailed. 3 That's why I brought in Weste. And if we look at figure -- I have a cross-sectional view of a figure 4 5 where I've used Weste to show the P-plus in an 6 N-well to implement the diode. And I'm trying to 7 find it. 8 0. Take your time. But I am interested in 9 seeing it and discussing it so... All right. I put this in the other 10 Α. 11 declaration, but it's in the McAdams declaration on 12 page 122 of 136, or page 119. 13 Q. Okay. I have it here. So we see simply by putting the P-plus in 14 Α. the N-well, that a diode is formed, which will 15 connect node 14 of McAdams to Vdd. 16 Also, with the '492 implementation, it 17 would be node out in Figure 2A to V internal. 18 19 So it's just simply adding the P-plus in the N-well. 20 21 In this particular example, is the N-well 0. 22 at Vdd? Yes. And the substrate is at ground. 23 Α. And so the junction at the topmost 24 Q. P-well -- I'm sorry, would you call it a P-well or 25

1 a --2 A P-plus region. The plus indicates that Α. it's heavily doped, so when you make a connection to 3 metal, it's not rectifying or a Schottky contact. 4 Okay. So the interface between that 5 0. 6 topmost P-plus region and the N-well that it's in, that diode has an anode that's node 14 and a cathode 7 that's Vdd? 8 9 Yes. Power supply Vcc or Vdd. Α. 10 So I want to go back to 781, the Joo Q. discussion we were having. 11 12 Α. Okay. 13 And I mean, we were, I think, at page 54 of Q. 14 120. 15 Α. Okay. 16 And ask if it's your opinion that Joo alone Q. teaches this element? 17 18 MR. ANDERSON: Objection. Form. 19 THE WITNESS: Joo alone doesn't teach adding the diode as a detail. That would be 20 21 something that would just be adding an extra P-plus 22 region to the body of the NP1. 23 But Joo alone doesn't teach that. I mean, a person of ordinary skill in the art would know how 24 25 to do that. It's simply adding P-plus to the N-well.

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1	BY MR. JONES:
2	Q. The transistor MP1 in Joo does have, as we
3	talked about, two diodes, right? It has a source
4	body diode and a drain body diode?
5	A. Yes.
6	Q. And why would that, either of those diodes,
7	not meet this claim element?
8	A. Those are the source and drains of the
9	PMOS. So those are connected to the transistor.
10	So you would need to have the P-plus, as I
11	detailed in the other declaration, page 119 or page
12	122 of 136, where the N-well would have a P-plus for
13	a separate connection, because the source and drain
14	connections are already going to other places in the
15	circuit.
16	Q. I'm trying to understand how and perhaps
17	this is page 59 of 120. The Joo, I'm trying to
18	understand what would need to change in the Joo
19	circuit in order to meet the claim element.
20	I know you tried to explain that, so I
21	apologize for the same thing. But can you help me
22	understand better, hopefully with reference to the
23	declaration, the Joo declaration, what manipulation
24	would need to occur?
25	A. It's quite simple.

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	R. Jacob Baker, Ph.D., P.E. Samsung Electronics vs. Promos Technologies
1	Q. Sure.
2	A. I'll just draw it on the side here as a
3	P-plus. And that goes to Vcc. And then that would
4	provide a diode like this to Vcc.
5	So you just add a P-plus, just like it's
6	drawn in the other declaration. Of course the P-plus
7	would be at the top. I just kept it real simple.
8	Q. And the diode, the anode of the diode is
9	always the P-type region? Is that right?
10	A. I'm sorry. I mislabeled this. This
11	doesn't go to Vcc. It's already connected to Vcc.
12	It goes over to the input. We'll just call it X
13	here; X. It's simpler if you look at page 122 of 136
14	in the other declaration.
15	Q. Okay. So in order to meet the claim
16	element, a person of skill in the art would need to
17	add a P-type region in the correct place near MP1 and
18	that P-type region would need to connect to the node
19	N2; is that correct?
20	MR. ANDERSON: Objection. Form.
21	THE WITNESS: Well, it's discussed in the
22	declaration. But in real simple terms, all you do is
23	put a P-plus in the N-well. Tie that P-plus to node
24	14 in McAdams, for example. Or across the fuse to
25	node X in Figure 2.

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Samsung Electronics vs. Promos Technologies R. Jacob Baker, Ph.D., P.E. Just in simple terms, you just add a P-plus 1 2 to the N-well. 3 And because I'm doing this on the fly, and I haven't written this in the declaration, give me a 4 5 second, because the diode I've drawn here may 6 actually need to be connected there to connect to 7 meet the claim language. 8 And again, I haven't written this up here. So give me a second and I'll -- I mean, the takeaway 9 10 is the P-plus. You just add a P-plus to the N-well. 11 BY MR. JONES: 12 Sure. As you're doing that, and maybe this 0. is for Paul too, but it's important to get the 13 14 correct answer today. 15 And, Dr. Baker, you should understand procedurally it's our position that Samsung's case 16 will be limited; that the 781 IPR concerning Joo will 17 be limited to specifically to what's written in your 18 19 781 declaration. 20 I'm sure Paul would object and argue 21 otherwise. 22 But at least today my purpose in this is to at least get your full and accurate opinion on this. 23 So take the time you need. But hopefully, for your 24 25 sake, you can tie that into the 781 declaration

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1	somehow in our discussion.
2	A. Oh, I thought I was. I was simply it
3	seems like the discussion is very clear here
4	Q. Okay.
5	A on how the combination of Joo and Weste
6	would be implemented.
7	I was simply trying to explain to you and
8	be helpful as to how P-plus would have been included
9	in another way that I've described in one of the
10	other declarations.
11	But I mean, we can stick to this
12	declaration, and I think that the combination is
13	clear. If we look at the figure on page 61 of 120,
14	that we can see the diodes that meet the claim
15	language, and the connection of the fuse and the fuse
16	to Vcc.
17	I was simply perhaps I shouldn't have
18	been, but I was trying to be helpful and explain how
19	another diode could be implemented based upon what I
20	did in the other declaration.
21	Q. Okay. So I must have misunderstood. I'm
22	not trying to push you into saying that it wasn't in
23	your declaration.
24	But let's talk about that. Page 61 of 120,
25	I think you've just referenced it.

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1	A. Yes.			
2	Q. And how that picture on the top of that			
3	page meets the claim element, then. And I think that			
4	would be more appropriate.			
5	Which diode meets the claim element?			
6	A. The diode that's in blue that's connected			
7	from N2 to Vcc. That's labeled body diode.			
8	Q. And does that diode exist in MP1 of Joo?			
9	A. Yes.			
10	Q. Okay. So is it your opinion that Joo alone			
11	meets the claim element?			
12	A. I think the answer is yes, but I think that			
13	it may be more clear to bring in Weste to make sure			
14	that it was really clear.			
15	Q. I'm asking it another way. Is it possible			
16	to make MP1 in such a way that there is not a diode			
17	across the fuse?			
18	MR. ANDERSON: Objection. Form.			
19	THE WITNESS: If you look at MP1 in there,			
20	it's not possible. There's a P-plus connected to N2.			
21	There's the N-well and N-plus that are tied to Vcc,			
22	which is the body of MP1. So the answer is no.			
23	BY MR. JONES:			
24	Q. So in Joo, for each of the transistors,			
25	there's actually two PMOS, two NMOS, and an inverter,			

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1	which is presumably made of two or more transistors.				
2	Each of the transistors in that circuit has				
3	two diodes, right?				
4	MR. ANDERSON: Objection. Form.				
5	THE WITNESS: There's a parasitic diode				
6	between the source and drain, and the body of all of				
7	these MOS transistors, yes.				
8	BY MR. JONES:				
9	Q. I guess because you have a clean copy of				
10	Joo, can I ask you to draw in where each of those				
11	parasitic diodes would be on Joo Figure 2? And it				
12	may be better on Figure 2 if you turn, just because				
13	it's bigger.				
14	A. (Witness complies.) Just for the PMOS?				
15	Q. For the NMOS, too. For I guess all of the				
16	transistors that are shown.				
17	A. It's the same as what's drawn on page 61 of				
18	my declaration. Sorry it's not as clear as I would				
19	like. But also I'll just write				
20	Q. I'm going to take my pen back.				
21	A. Oh, sorry.				
22	Q. Thanks.				
23	A. It's clearer on the figure that I have on				
24	page 61 of 120 of the declaration, but I tried to				
25	draw the same thing.				

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1	Q. Okay. And then I assume MN2 will have also				
2	two diodes to ground?				
3	A. Yep.				
4	Q. Just for completeness.				
5	A. (Witness complies.)				
6	MR. JONES: So I said we wouldn't do this,				
7	but I'm going to mark this as an exhibit because it's				
8	a unique document now. So could we put Exhibit 1 on				
9	this.				
10	MR. ANDERSON: Unless you want to start				
11	where you guys are going to be at for consistency.				
12	You guys usually start with 2000.				
13	MR. BANSAL: Do you want me to give you				
14	your last exhibit number?				
15	MR. JONES: Yeah. If it's handy and you				
16	can pull it up.				
17	MR. ANDERSON: Otherwise it gets kind of				
18	weird.				
19	MR. JONES: Actually, so I'm going to mark				
20	it only in the 781 IPR because it's Joo, so I'll mark				
21	it 2002.				
22	MR. BANSAL: That's fine.				
23	MR. JONES: Which I don't think we've used				
24	yet.				
25	MR. BANSAL: No. That's okay.				

	R. Jacob Baker,	, Ph.D., P.E. Samsur	ng Electronics vs. Promos Technologies		
1		(Exhibit 2002 wa	s marked for		
2		identification.)			
3		MR. JONES: And we in	dicated it's for the		
4	781 IPR.	It's on the record, s	o we'll be fine.		
5		MR. ANDERSON: Yep.			
6		MR. JONES: I think w	e're done with this		
7	document,	but here's the rest -	- why don't we go off		
8	the record.				
9		(A recess was ta	ken from 12:15 p.m.		
10	to 12:25 p.m.)				
11		MR. JONES: So I have	no more questions.		
12	Thank you, Dr. Baker.				
13		MR. ANDERSON: I have	no questions. Thank		
14	you.				
15			-		
16	(The	deposition was conclu	ded at 12:25 p.m.)		
17			-		
18					
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1 CERTIFICATE OF REPORTER I, the undersigned, a Certified Shorthand 2 3 Reporter of the State of Nevada, do hereby certify: That the foregoing proceedings were taken 4 5 before me at the time and place herein set forth; that any witnesses in the foregoing proceedings, 6 7 prior to testifying, were duly sworn; that a record of the proceedings was made by me using machine 8 shorthand which was thereafter transcribed under my 9 10 direction; that the foregoing transcript is a true record of the testimony given to the best of my 11 12 ability. 13 Further, that before completion of the proceedings, review of the transcript [X] was 14 15] was not requested pursuant to NRCP 30(e). Г 16 I further certify I am neither financially 17 interested in the action, nor a relative or employee 18 of any attorney or party to this action. 19 IN WITNESS WHEREOF, I have this date 20 subscribed my name. 21 Dated: October 28, 2019 22 23 24 GALE SALERNO, RMR, CCR #542 25

R. Jacob Baker, Ph.D., P.E. Samsung Electronics vs. Promos Technologies 1 DECLARATION UNDER PENALTY OF PERJURY 2 Case Name: Samsung Electronics vs. Promos Technologies 3 Date of Deposition: 10/25/2019 Job No.: 10061825 4 5 I, R. JACOB BAKER, PH.D., P.E., hereby certify 6 7 under penalty of perjury under the laws of the State of NEVADA that the foregoing is true and correct. 8 Executed this 13^{H} day of 9 NOVEMBER, 2019, at /AS VEGAS. 10 11 12 13 14 R. JÁCOB BAKER, PH.D., P.E. 15 16 NOTARIZATION (If Required) State of _____ 17 18 County of _____ 19 Subscribed and sworn to (or affirmed) before me on this _____ day of _____, 20__, 20 by_____, proved to me on the 21 22 basis of satisfactory evidence to be the person who appeared before me. 23 Signature: _____ (Seal) 24 25

Samsung Electronics vs. Promos Technologies

1 DEPOSITION ERRATA SHEET Case Name: Samsung Electronics vs. Promos Technologies 2 Name of Witness: R. Jacob Baker, Ph.D., P.E. Date of Deposition: 10/25/2019 3 Job No.: 10061825 Reason Codes: 1. To clarify the record. 4 2. To conform to the facts. 5 3. To correct transcription errors. Page /4 Line /2 Reason _/ 6 (Lowerchse) to NV From NUT 7 Page / 5 Line _ 9_ Reason _ / 8 From N/ AU7 9 to OU Line Page 11 ⊃ Reason / 10 to lodge to rise to latch (From Milse 11 Page 56 Line /) Reason / 12 to (13 From Page 4C Line Reason 14 From and Oliviun to gall 15 Reason _ Page 52 Line 16 to Terminate From TRLAWSMIL 17 _Line 9 Page 54 Reason \mathcal{I} 18 MICROGRAMS to MICROAMPS 19 From Page 57 Line 4 Reason / 20 ChANG to WILL NO From Will 21 22 Page Line Reason 23 From to Page Line Reason 24 25 From to

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